


MITSUBISHI IGBT  
**CY25AAJ-8F**

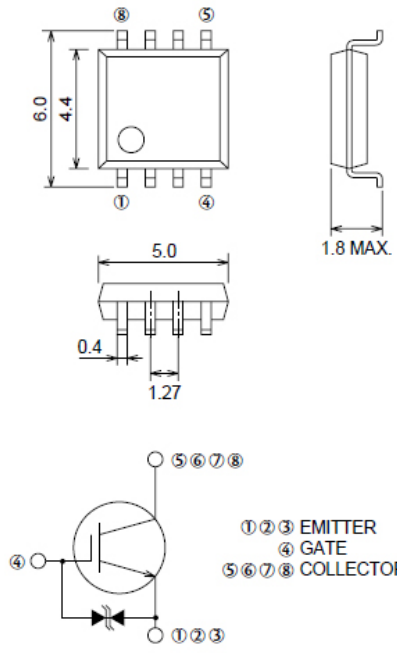
Nch IGBT for STROBE FLASHER

**CY25AAJ-8F**



● VCES ..... 400V  
 ● ICM ..... 150A  
 ● Drive voltage ..... 4V

**OUTLINE DRAWING** Dimensions in mm



①②③ EMITTER  
 ④ GATE  
 ⑤⑥⑦⑧ COLLECTOR

**SOP-8**

APPLICATION  
 Strobe Flasher for camera

**MAXIMUM RATINGS** (Tc = 25°C)

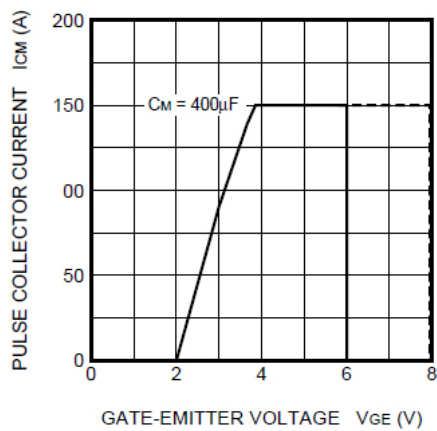
Symbol	Parameter	Conditions	Ratings	Unit
VCES	Collector-emitter voltage	VGE = 0V	400	V
VGES	Gate-emitter voltage	VCE = 0V	±6	V
VGEM	Peak gate-emitter voltage	VCE = 0V, tw = 10s	±8	V
ICM	Collector current (Pulsed)	CM = 400μF see figure 1	150	A
Tj	Junction temperature		-40 ~ +150	°C
Tstg	Storage temperature		-40 ~ +150	°C

Sep. 2000

**ELECTRICAL CHARACTERISTICS** ( $T_j = 25^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$I_c = 1\text{mA}, V_{GE} = 0\text{V}$	450	—	—	V
$V_{(BR)GES}$	Gate-emitter breakdown voltage	$I_G = \pm 100\mu\text{A}, V_{CE} = 0\text{V}$	$\pm 8$	—	—	V
$I_{CES}$	Collector-emitter leakage current	$V_{CE} = 400\text{V}, V_{GE} = 0\text{V}$	—	—	10	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current	$V_{GE} = \pm 6\text{V}, V_{CE} = 0\text{V}$	—	—	$\pm 10$	$\mu\text{A}$
$V_{GE(th)}$	Gate-emitter threshold voltage	$V_{CE} = 10\text{V}, I_c = 1\text{mA}$	—	—	1.5	V

Figure1. MAXIMUM PULSE COLLECTOR CURRENT



**APPLICATION EXAMPLE**

